

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TD62308BP-1, TD62308BF

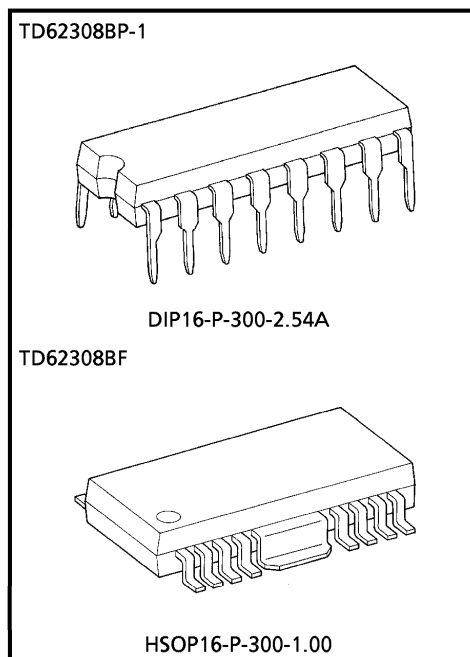
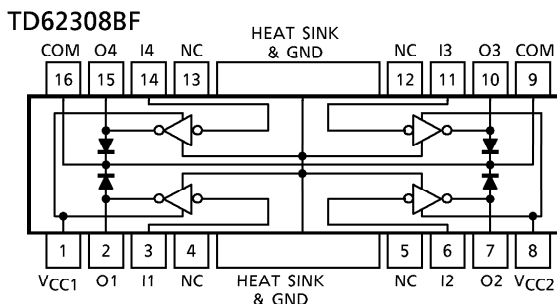
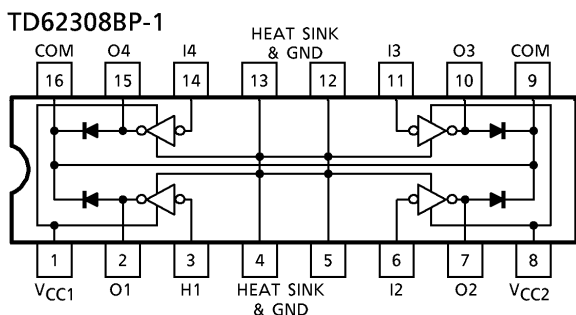
4ch LOW INPUT ACTIVE HIGH-CURRENT DARLINGTON SINK DRIVER

The TD62308BP-1 and TD62308BF are non-inverting transistor array which are comprised of four NPN darlington output stages and PNP input stages. This device is low level input active driver and are suitable for operation with TTL, 5V CMOS and 5V Microprocessor which have sink current output drivers. Applications include relay, hammer, lamp and stepping motor drivers.

FEATURES

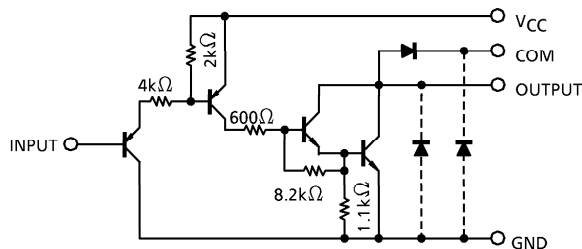
- Two VCC Terminals VCC1, VCC2 (Separated)
- Package Type BP-1 : DIP-16pin
BF : PFP-16pin
- High Sustaining Voltage Output : $V_{CE(SUS)} = 80V$ (Min.)
- Output Current (Single Output) : $I_{OUT} = 1.5A$ (Max.)
- Output Clamp Diodes
- Low Level Active Input
- GND and SUB Terminal = Heat Sink
- Input Compatible with TTL and 5V CMOS
- Standard Supply Voltage

PIN CONNECTION (TOP VIEW)



Weight
 DIP16-P-300-2.54A : 1.11g (Typ.)
 HSOP16-P-300-1.00 : 0.50g (Typ.)

SCHEMATICS (EACH DRIVER)



(Note) The output parasitic diode cannot be used as clamp diode.

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• TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	V _{CC}	7	V	
Output Sustaining Voltage	V _{CE(SUS)}	-0.5~80	V	
Parasitic Transistor Output Voltage	V _{CEF(*1)}	80	V	
Output Current	I _{OUT}	1.5	A / ch	
Input Current	I _{IN}	-10	mA	
Input Voltage	V _{IN}	7	V	
Clamp Diode Reverse Voltage	V _R	80	V	
Clamp Diode Forward Current	I _F	1.5	A	
Power Dissipation	BP-1	P _D	1.47 / 2.7 (*2)	W
	BF		0.9 / 1.4 (*3)	
Operating Temperature	T _{opr}	-40~85	°C	
Storage Temperature	T _{stg}	-55~150	°C	

(*1) Parasitic Transistor (COMMON - GND - OUTPUT) Output Voltage

(*2) On Glass Epoxy PCB (50 × 50 × 1.6mm Cu 50%)

(*3) On Glass Epoxy PCB (60 × 30 × 1.6mm Cu 30%)

RECOMMENDED OPERATING CONDITIONS (Ta = -40~85°C)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT					
Supply Voltage	V _{CC}	—	4.5	—	5.0	V					
Output Sustaining Voltage	V _{CE(SUS)}	—	0	—	80	V					
Output Current	I _{OUT}	DC 1 Circuit, Ta = 25°C T _{pw} = 25ms 4 Circuits T _j = 120°C Ta = 85°C				A / ch					
							BP-1 (*1)	Duty = 10%	0	—	1.20
								Duty = 50%	0	—	0.35
							BF (*2)	Duty = 10%	0	—	0.75
								Duty = 50%	0	—	0.18
Input Voltage	V _{IN}	—	0	—	25	V					
	Output On	V _{IN(ON)}	—	0	—	V _{CC} -3.6	V				
	Output Off	V _{IN(OFF)}	—	V _{CC} -1.0	—	V _{CC}					
Clamp Diode Reverse Voltage	V _R	—	—	—	80	V					
Clamp Diode Forward Current	I _F	—	—	—	1.25	A					
Power Dissipation	BP-1	P _D	Ta = 85°C (*1)	—	—	1.4	W				
	BF							Ta = 85°C (*2)	—	—	0.7

(*1) On Glass Epoxy PCB (50 × 50 × 1.6mm Cu 50%)

(*2) On Glass Epoxy PCB (60 × 30 × 1.6mm Cu 30%)

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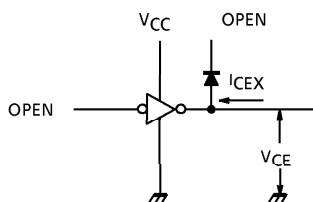
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ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

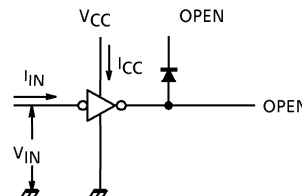
CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Input Voltage	"H" level	V_{IH}	—	$V_{CC} - 1.6$	—	V_{CC}	V	
	"L" level	V_{IL}	—	—	—	$V_{CC} - 3.6$		
Input Current	"H" level	I_{IH}	2	—	—	10	μA	
	"L" level	I_{IL}	2	$V_{CC} = 5.5V, V_{IN} = 0.4V$	-0.05	-0.36	mA	
Output Leakage Current	I_{CEX}	1	$V_{OUT} = 80V, Ta = 25^{\circ}C$	—	—	50	μA	
			$V_{OUT} = 80V, Ta = 85^{\circ}C$	—	—	100		
Output Saturation Voltage	$V_{CE(sat)}$	3	$V_{CC} = 4.5V, I_{OUT} = 1.25A$	—	1.3	1.8	V	
Clamp Diode Reverse Current	I_R	4	$V_R = 80V, Ta = 25^{\circ}C$	—	—	50	μA	
Clamp Diode Forward Voltage	V_F	5	$I_F = 1.25A$	—	1.5	2.0	V	
Supply Current	Output On	$I_{CC(ON)}$	2	$V_{CC} = 5.5V, V_{IN} = 0V$	—	8.5	12.5	mA / ch
	Output Off	$I_{CC(OFF)}$	2	$V_{CC} = 5.5V, V_{IN} = V_{CC}$	—	—	10	μA
Turn-On Delay	t_{ON}	6	$V_{OUT} = 80V, R_L = 68\Omega$	—	0.2	—	μs	
Turn-Off Delay	t_{OFF}			—	5.0	—		
Parasitic Transistor Output Voltage	V_{CEF}	7	$I_{CEF} = 150mA$	80	—	—	V	

TEST CIRCUIT

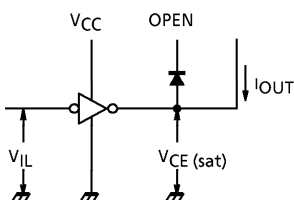
1. I_{CEX}



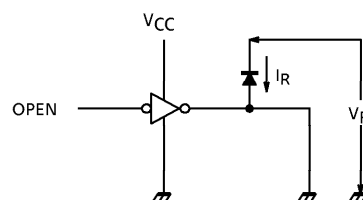
2. I_{CC}, I_{IN}



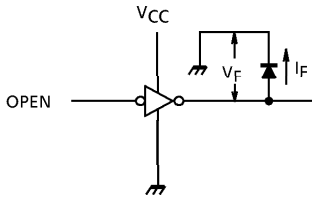
3. $V_{CE(sat)}$



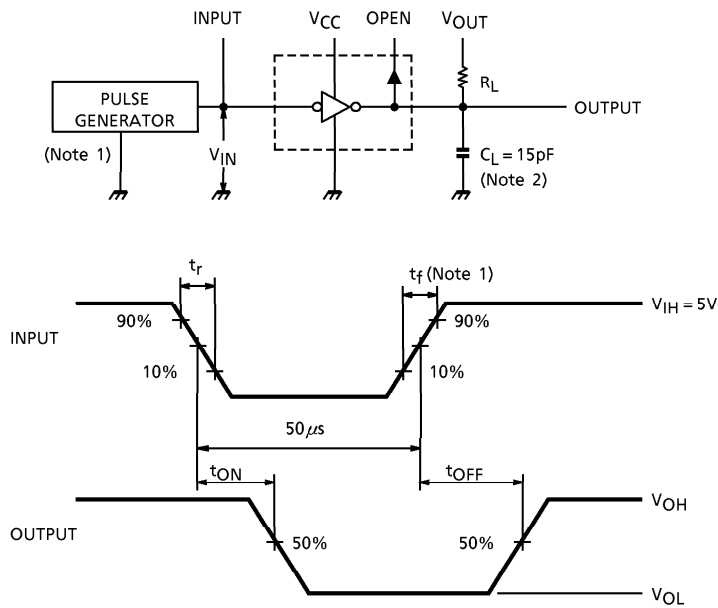
4. I_R



5. V_F

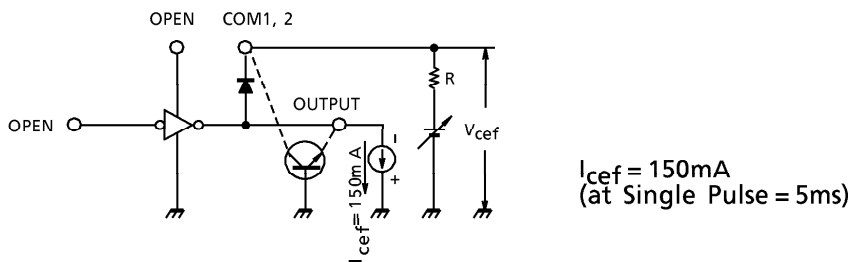


6. t_{ON} , t_{OFF}



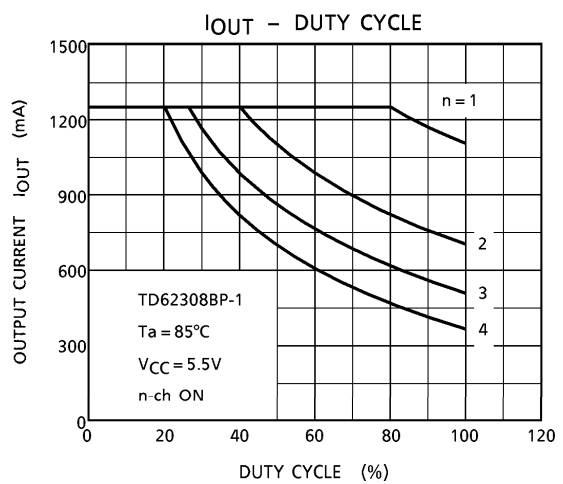
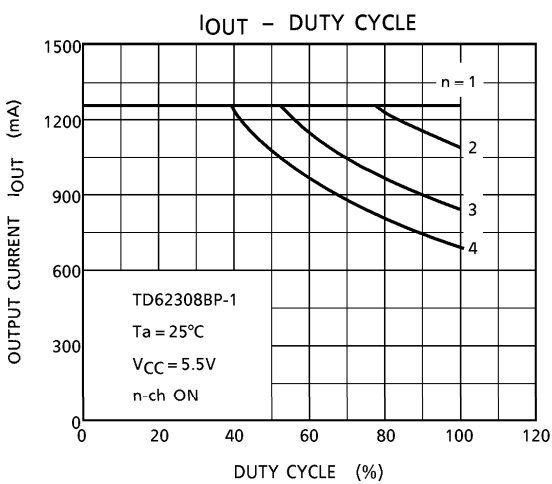
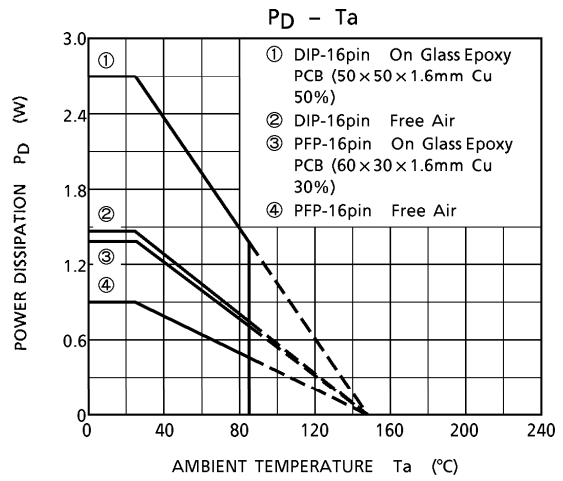
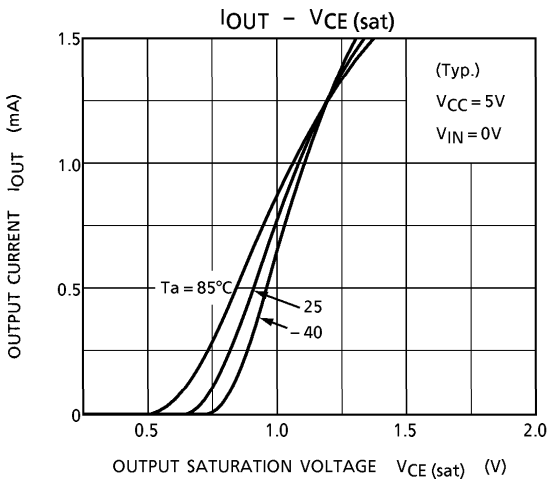
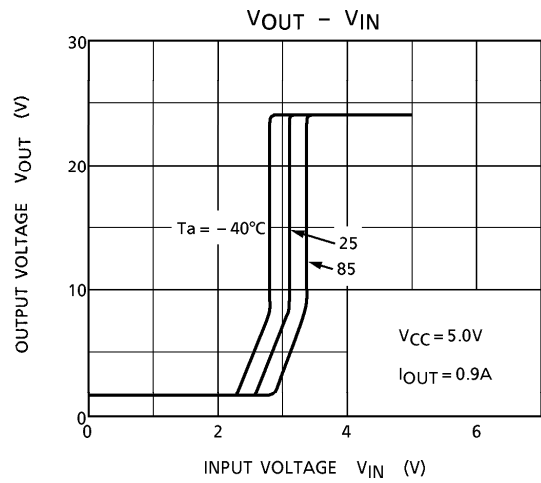
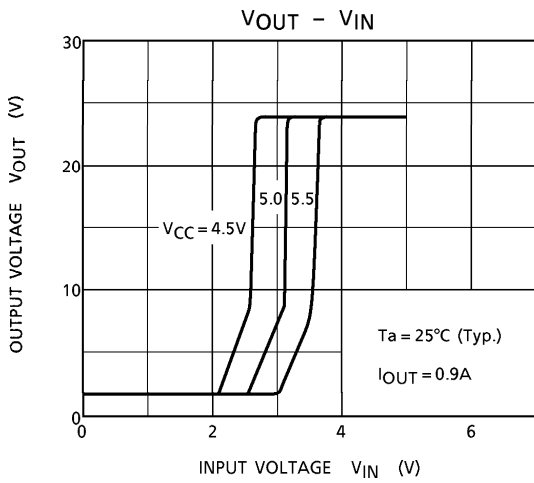
(Note 1) Pulse Width $50\mu s$, Duty Cycle 10%、
Output Impedance 50Ω , $t_r \leq 5ns$, $t_f \leq 10ns$
(Note 2) C_L includes probe and jig capacitance

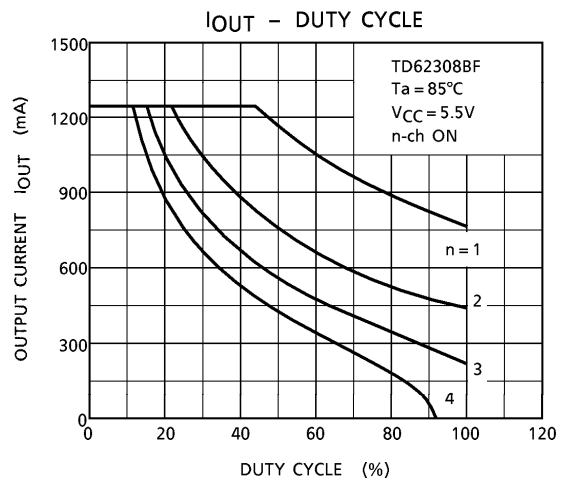
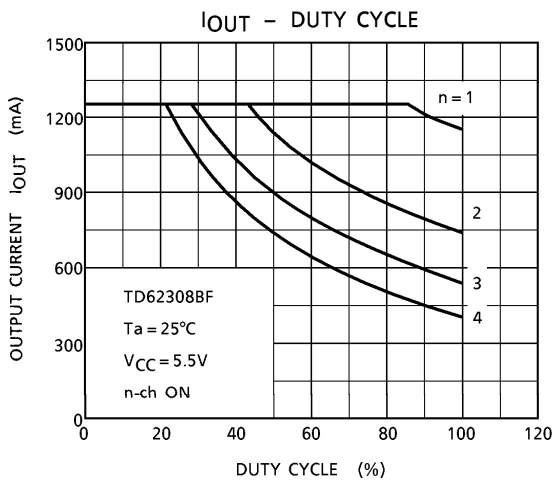
7. V_{cef}



PRECAUTIONS for USING

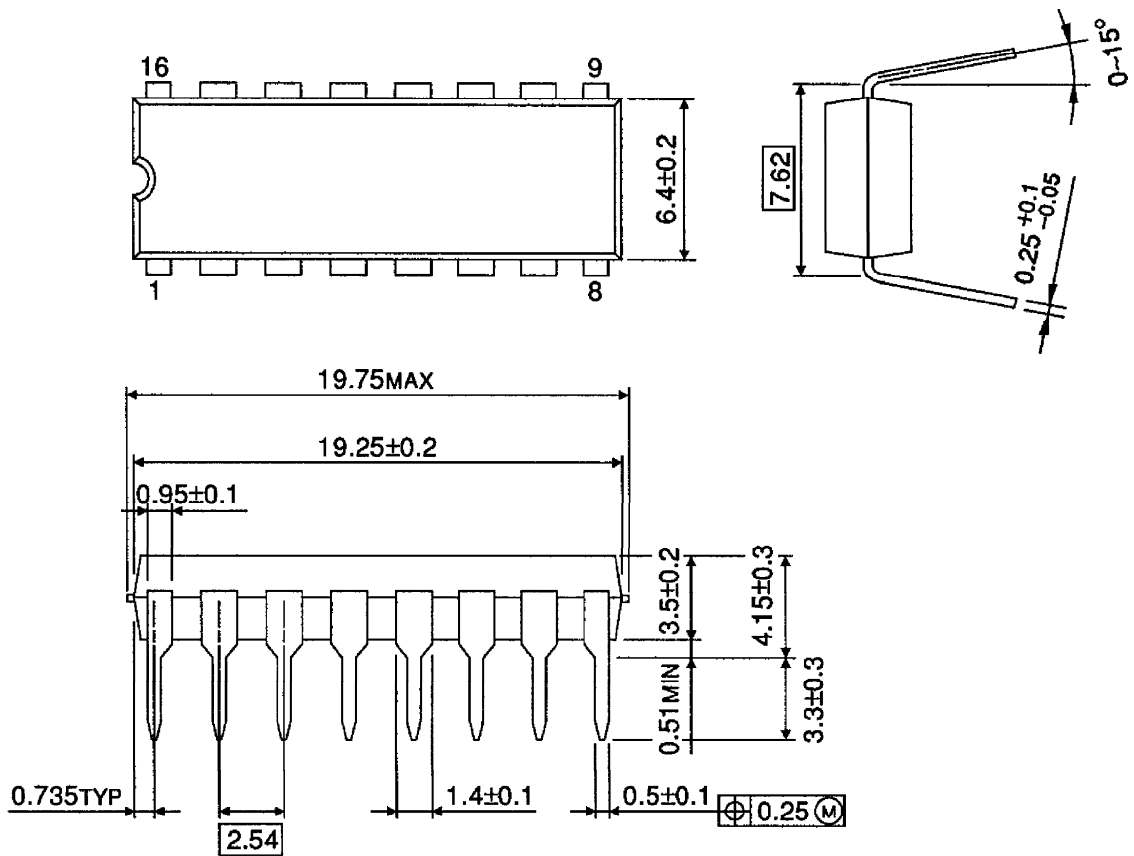
Utmost care is necessary in the design of the output line, V_{CC} , COMMON and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.





OUTLINE DRAWING
DIP16-P-300-2.54A

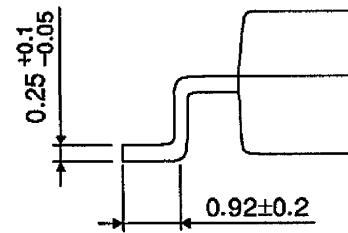
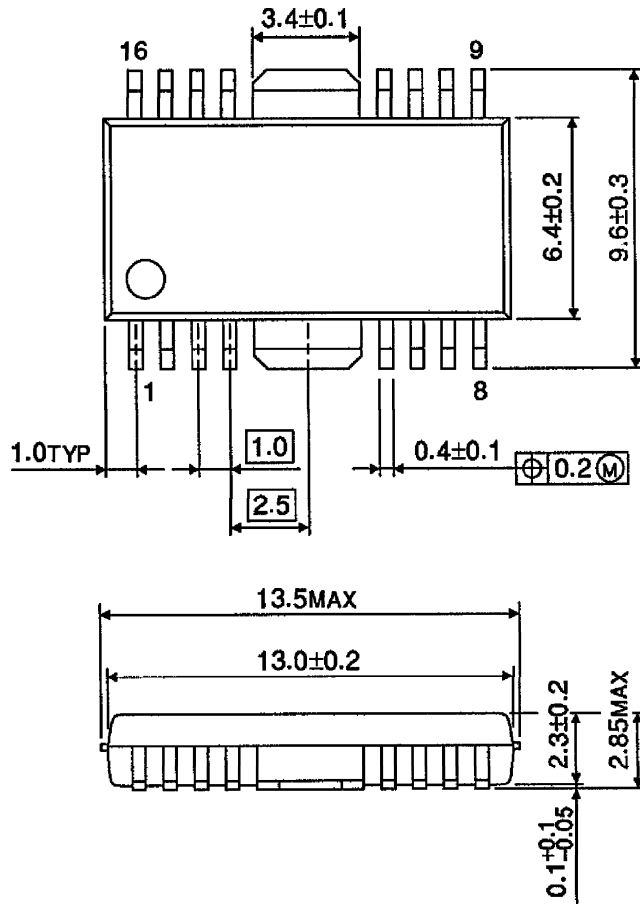
Unit : mm



Weight : 1.11g (Typ.)

OUTLINE DRAWING
HSOP16-P-300-1.00

Unit : mm



Weight : 0.50g (Typ.)